

2SB1362

Silicon PNP Triple-Diffused Planar Type

High Power Amplifier

Complementary Pair with 2SD2052

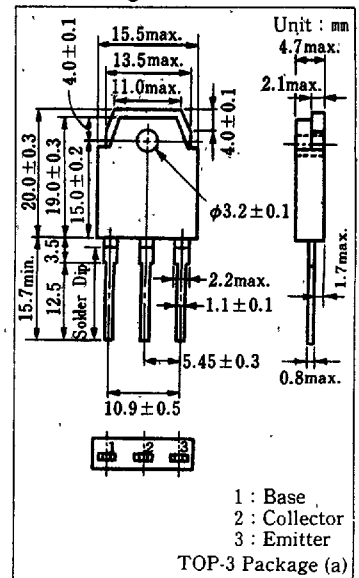
■ Features

- Very good linearity of DC current gain (h_{FE})
- Wide area of safety operation (ASO)
- High transition frequency (f_T)

■ Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Item	Symbol	Value	Unit
Collector-base voltage	V_{CBO}	-150	V
Collector-emitter voltage	V_{CEO}	-150	V
Emitter-base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-15	A
Collector current	I_C	-9	A
Collector power dissipation	$T_C=25^\circ\text{C}$	100	W
	$T_a=25^\circ\text{C}$	2.5	
Junction temperature	T_J	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

■ Package Dimensions

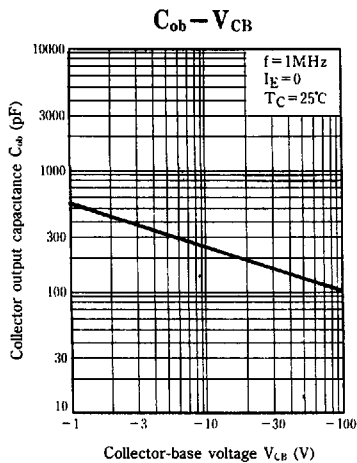
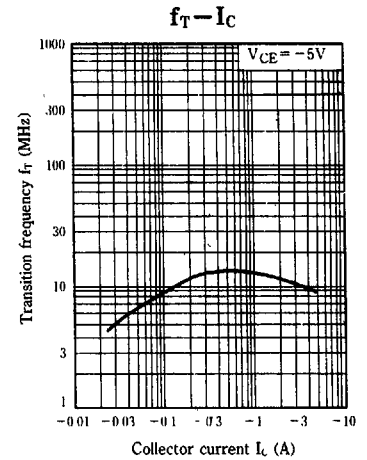
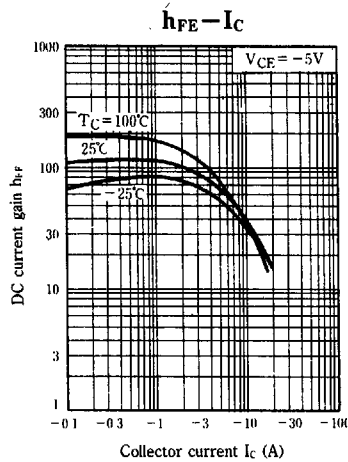
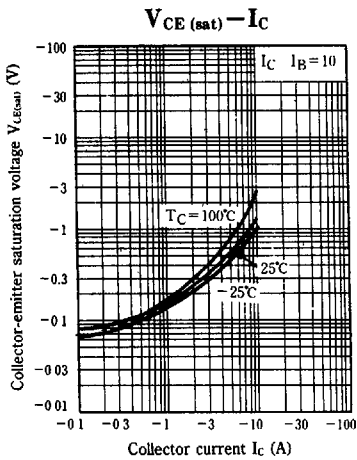
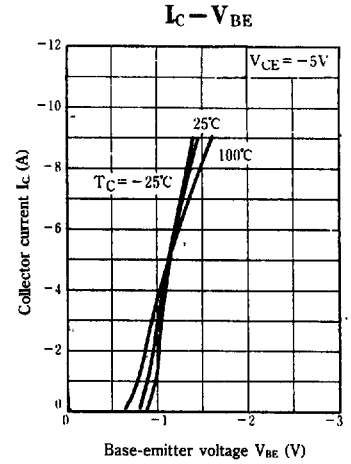
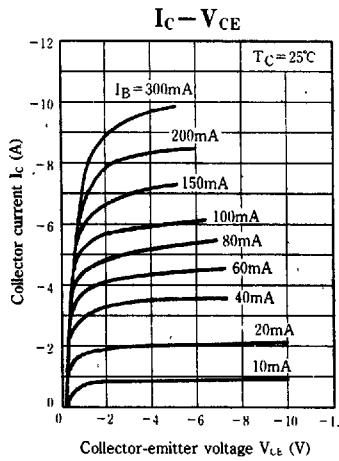
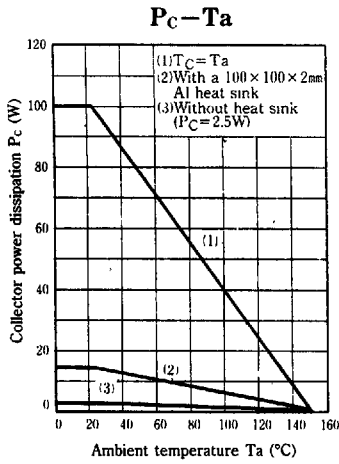


■ Electrical Characteristics ($T_c=25^\circ\text{C}$)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -150\text{V}, I_E = 0$			-50	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -3\text{V}, I_C = 0$			-50	μA
DC current gain	h_{FE1}	$V_{CE} = -5\text{V}, I_C = -20\text{mA}$	20			
	h_{FE2}^*	$V_{CE} = -5\text{V}, I_C = -1\text{A}$	60		200	
	h_{FE3}	$V_{CE} = -5\text{V}, I_C = -7\text{A}$	20			
Base-emitter voltage	V_{BE}	$V_{CE} = -5\text{V}, I_C = -7\text{A}$			-1.8	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -7\text{A}, I_B = -0.7\text{A}$			-2.0	V
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -0.5\text{A}, f = 1\text{MHz}$		15		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		270		pF

* h_{FE2} Classifications

Class	Q	S	P
h_{FE2}	60~120	80~160	100~200



Safety operation area-forward bias (ASO)

